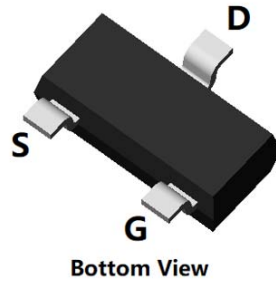
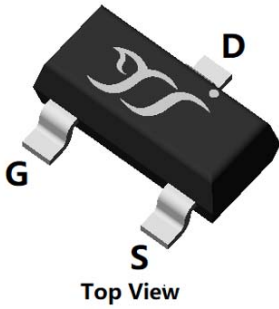
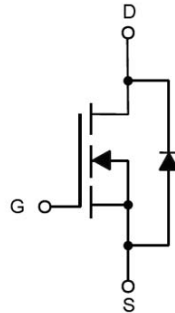


N-Channel Enhancement Mode Field Effect Transistor



SOT-23



Product Summary

• V_{DS}	60V
• I_D	3.0A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	< 100mohm
• $R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 120mohm

General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Fre
- Part no. with suffix "Q" means AEC-Q101 qualified

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	3	A
	$T_A=70^\circ\text{C}$		2.4	
Pulsed Drain Current ^A		I_{DM}	12	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	P_D	1.2	W
	$T_A=70^\circ\text{C}$		0.8	
Thermal Resistance Junction-to-Ambient ^B		$R_{\theta JA}$	104	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL03N06AQ	F2	S10.	3000	30000	120000	7" reel



YJL03N06AQ

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS1}	V _{GS} =±20V, V _{DS} =0V			±100	nA
	I _{GSS2}	V _{GS} =±10V, V _{DS} =0V			±50	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.9	1.3	2.0	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3A		86	100	mΩ
		V _{GS} =4.5V, I _D =2A		92	120	
Diode Forward Voltage	V _{SD}	I _S =3A, V _{GS} =0V			1.2	V
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHZ		409		pF
Output Capacitance	C _{oss}			50		
Reverse Transfer Capacitance	C _{rss}			41		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =30V, I _D =3A		10.27		nC
Gate-Source Charge	Q _{gs}			1.65		
Gate-Drain Charge	Q _{gd}			2.11		
Reverse Recovery Charge	Q _{rr}	I _F =3A, di/dt=100A/us		6.99		
Reverse Recovery Time	t _{rr}			32.6		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =30V, R _L =20Ω R _{GEN} =3Ω		3.6		ns
Turn-on Rise Time	t _r			17.6		
Turn-off Delay Time	t _{D(off)}			13		
Turn-off fall Time	t _f			23		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

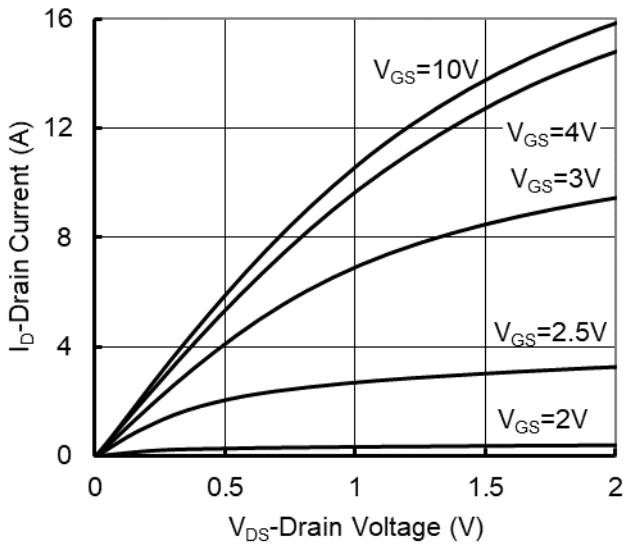


Figure1. Output Characteristics

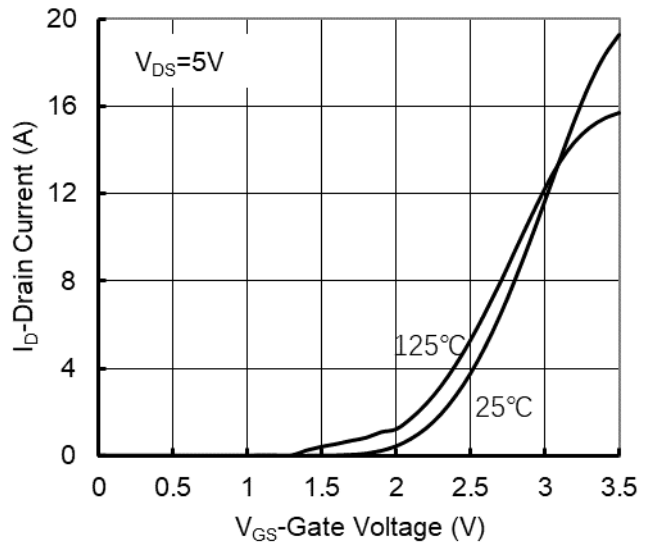


Figure2. Transfer Characteristics

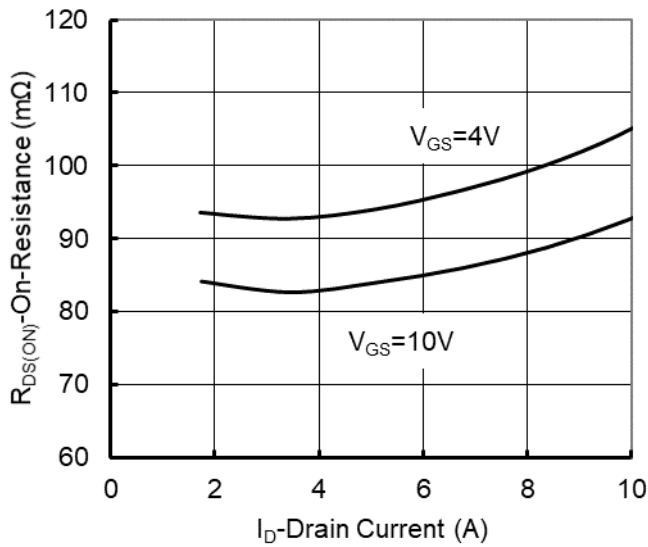


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

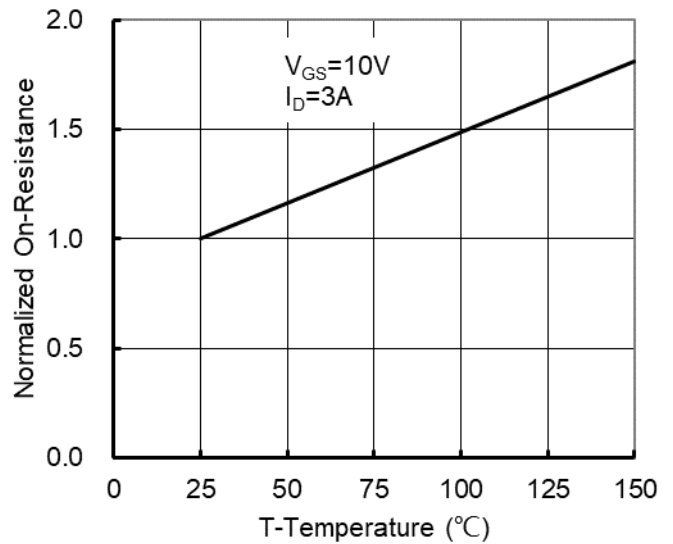


Figure 4: On-Resistance vs. Junction Temperature

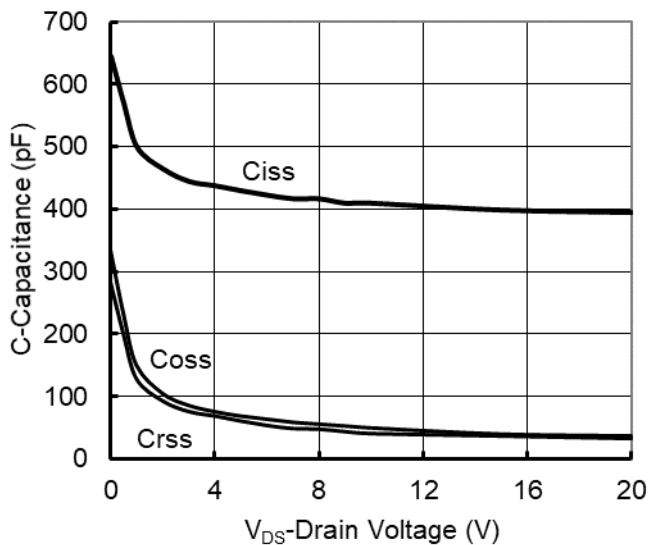


Figure5. Capacitance Characteristics

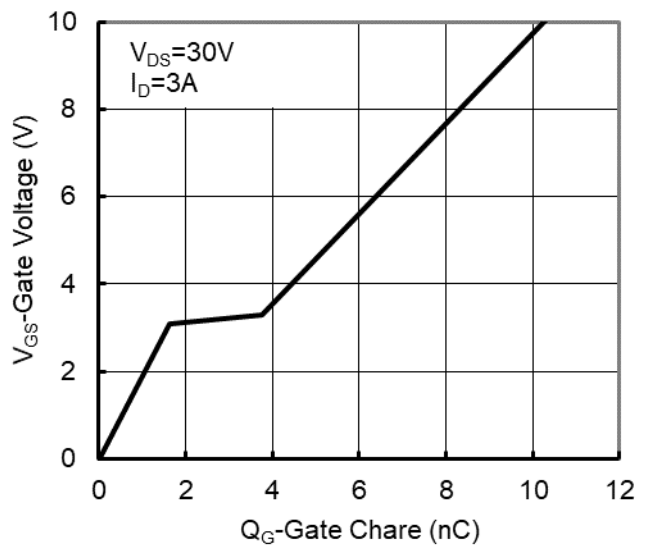


Figure6. Gate Charge



YJL03N06AQ

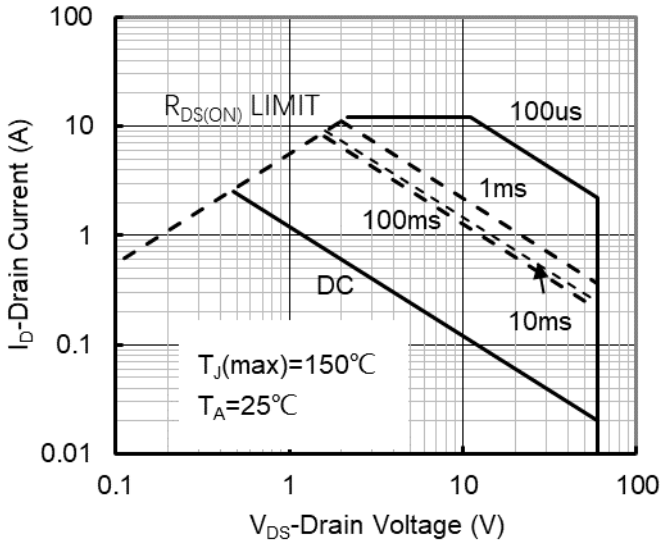


Figure7. Safe Operation Area

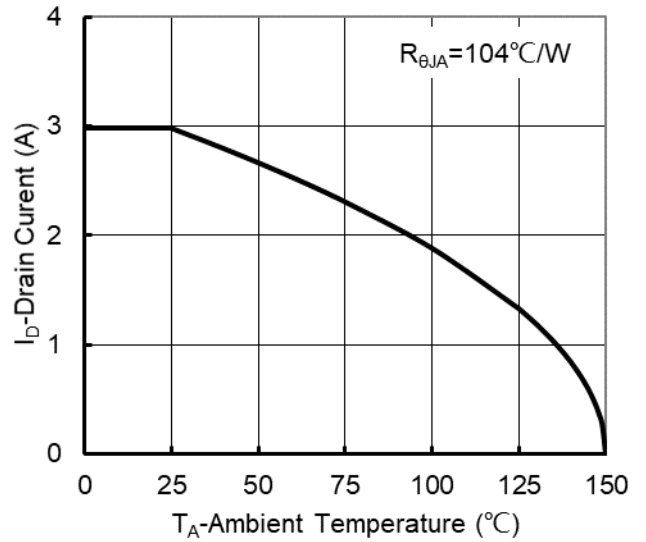


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

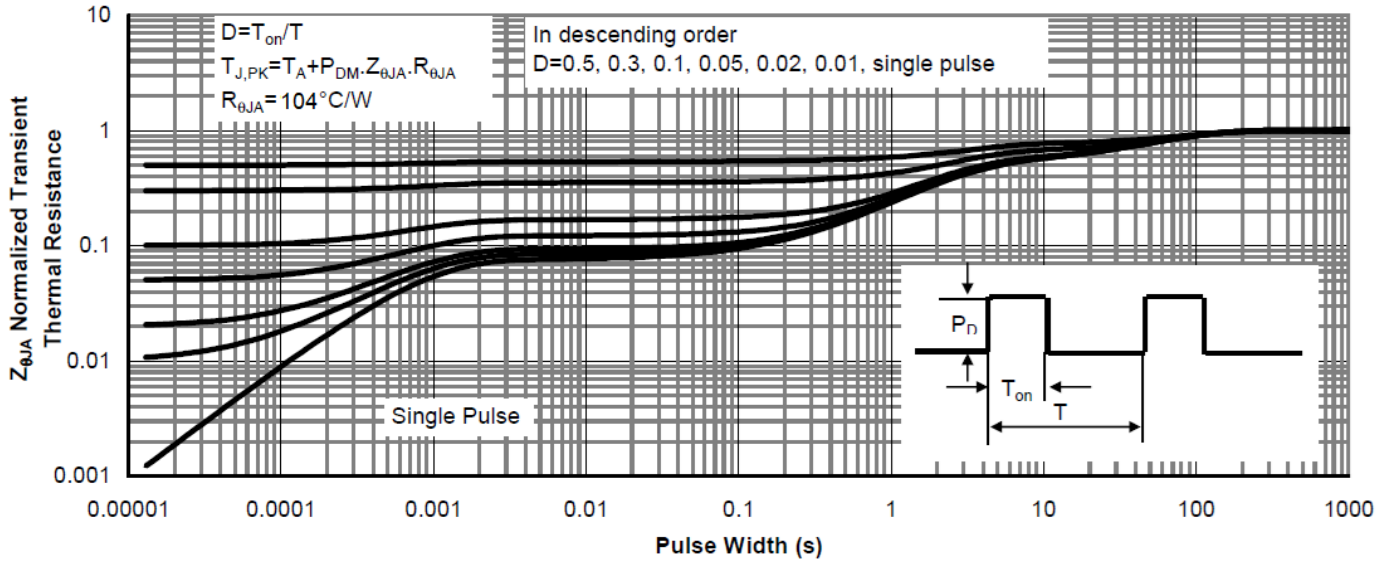


Figure9. Normalized Maximum Transient Thermal Impedance

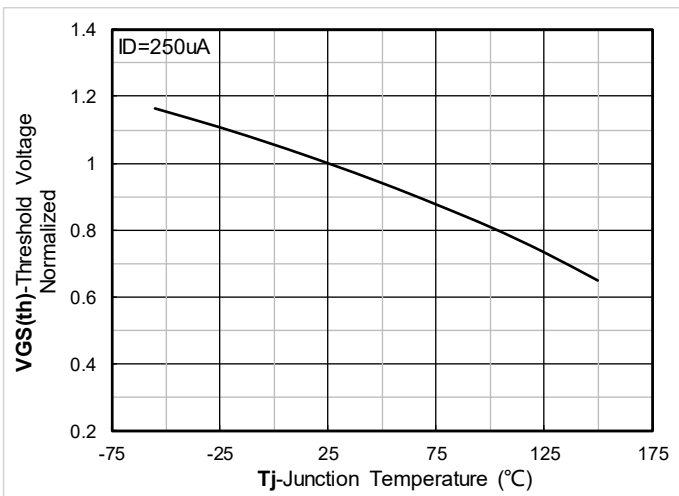
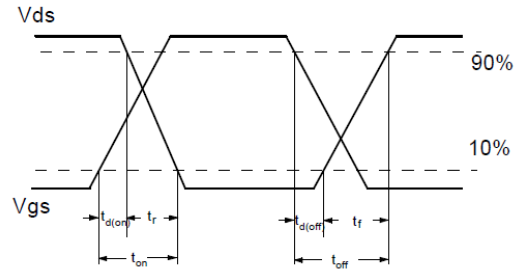
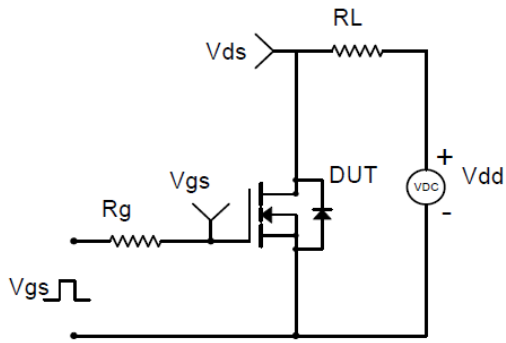
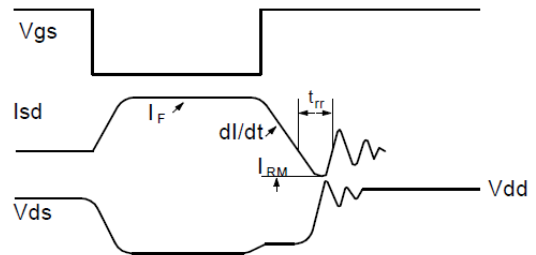
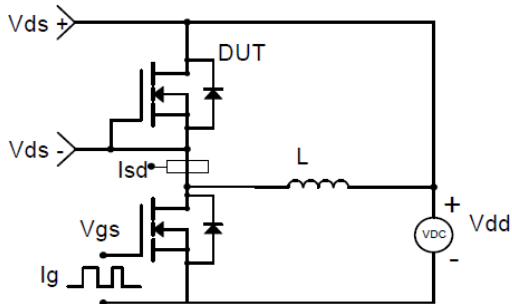


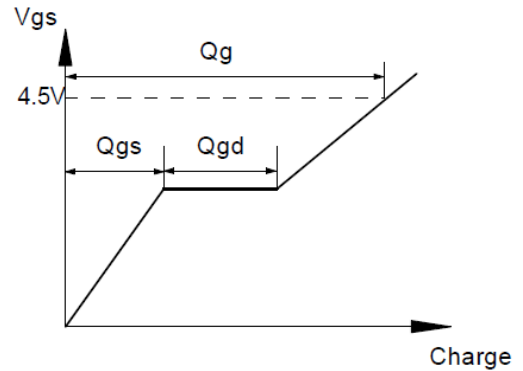
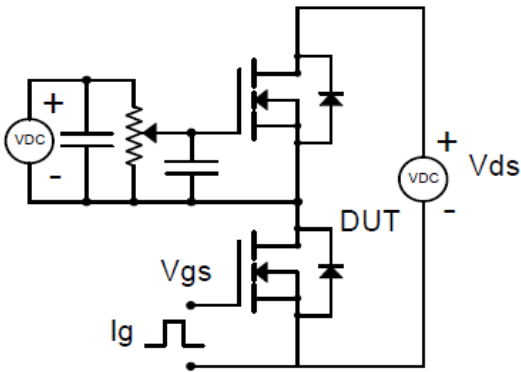
Figure 10. Normalized Threshold voltage



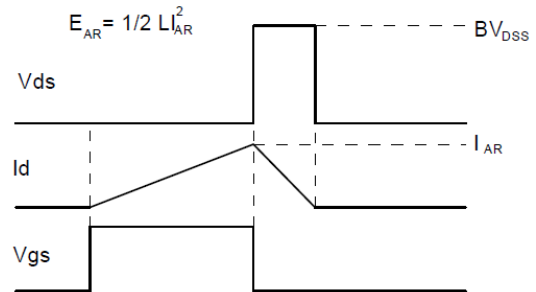
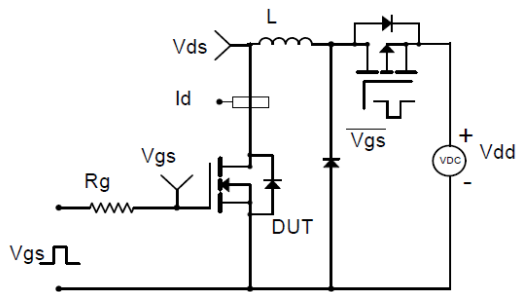
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

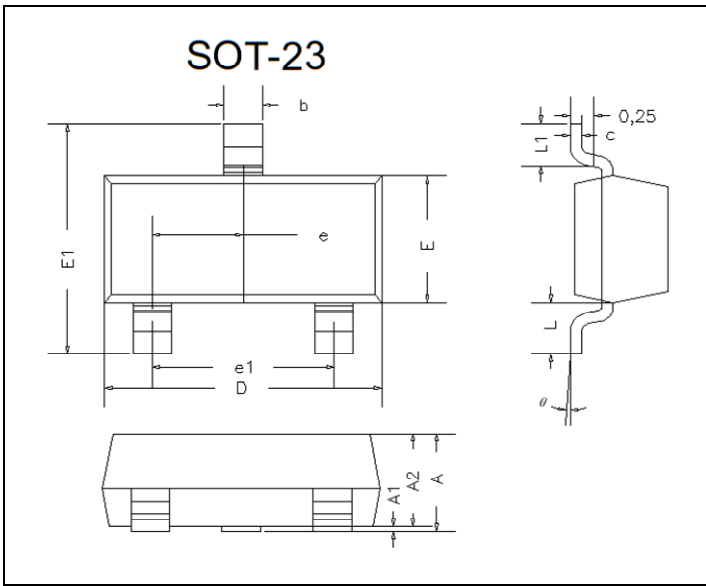


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



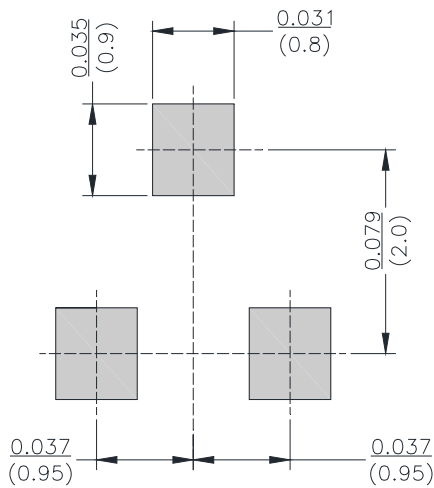
YJL03N06AQ

■ SOT-23 Package information



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.035	0.045	0.90	1.15	
A1	0.000	0.004	0.00	0.10	
A2	0.035	0.041	0.90	1.05	
b	0.012	0.020	0.30	0.50	
c	0.004	0.008	0.10	0.20	
D	0.110	0.118	2.80	3.00	
E	0.047	0.055	1.20	1.40	
E1	0.089	0.100	2.25	2.55	
e	0.370TYP		0.95TYP		
e1	0.071	0.079	1.80	2.00	
L	0.220REF		0.55REF		
L1	0.012	0.020	0.30	0.50	
theta	0°	8°	0°	8°	

■ SOT-23 Suggested Pad Layout





YJL03N06AQ

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with automotive electronics, are not designed for use in medical, life-saving, lifesustaining, or military, Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website [http:// www.21yangjie.com](http://www.21yangjie.com) , or consult your nearest Yangjie's sales office for further assistance.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Yangjie\(扬杰\)](#)